



Low capacitance bi-directional double ESD protection diode

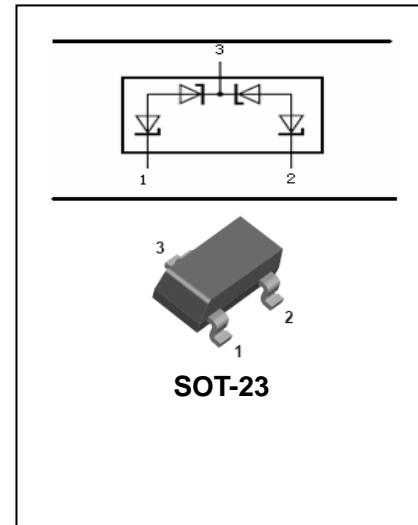
PESD5V0S2BT

FEATURES

- Bi-directional ESD protection of 2 lines.
- Low diode capacitance.
- Max. peak pulse power: $P_{PP}=130W$ at $t_P=8/20ms$.
- Low clamping voltage: $V_{CL(R)}=14V$ at $I_{PP}=12A$.
- Ultra low leakage current: $I_{RM}= 5nA$ at $V_{RWM} = 5V$.
- ESD protection>30 kV



Lead-free



APPLICATIONS

- Cellular handsets and accessories
- Portable electronics
- Computers and peripherals
- Communication systems
- Audio and video equipment

ORDERING INFORMATION

Type No.	Marking	Package Code
PESD5V0S2BT	G5	SOT-23

MAXIMUM RATING @ $T_a=25^\circ C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{RWM}	Reverse stand-off voltage	5	V
C_d	Diode capacitance	35	pF
P_{PP}	peak pulse power(8/20μs pulse)	130	W
I_{PP}	peak pulse current(8/20μs pulse)	12	A
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	°C



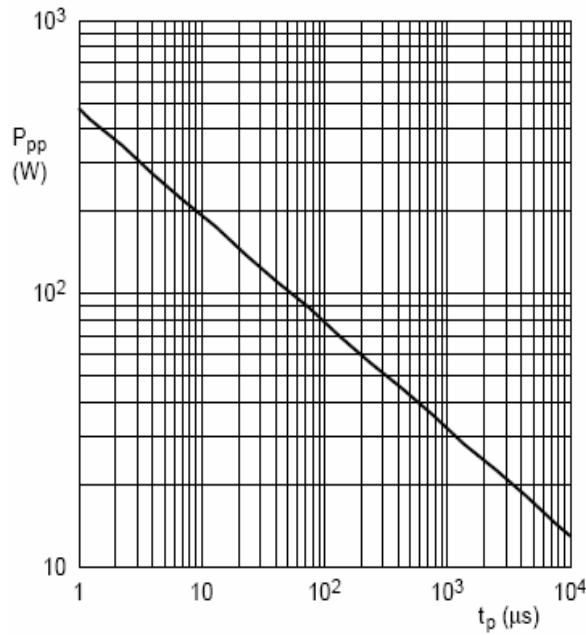
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ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
reverse stand-off voltage	V_{RWM}				5	V
reverse leakage current	I_{RM}	$V_{RWM}=5\text{V}$		5	100	nA
clamping voltage	$V_{(CL)R}$	$I_{PP}=1\text{A}$			10	V
		$I_{PP}=12\text{A}$			14	V
breakdown voltage	V_{BR}	$I_R=1\text{mA}$	5.5		9.5	V
Differential resistance	r_{diff}	$I_R=1\text{mA}$			50	Ω

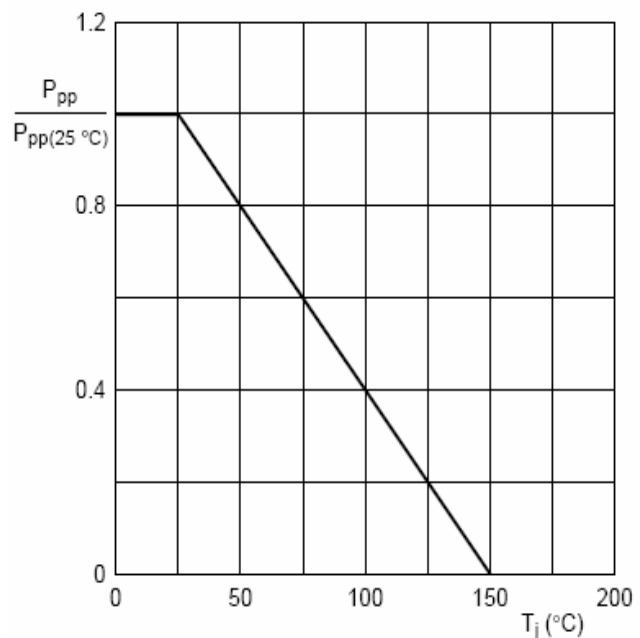
TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



$T_{amb} = 25^\circ\text{C}$.

$t_p = 8/20 \mu\text{s}$ exponential decay waveform;

Peak pulse power dissipation as a function of pulse time; typical values.



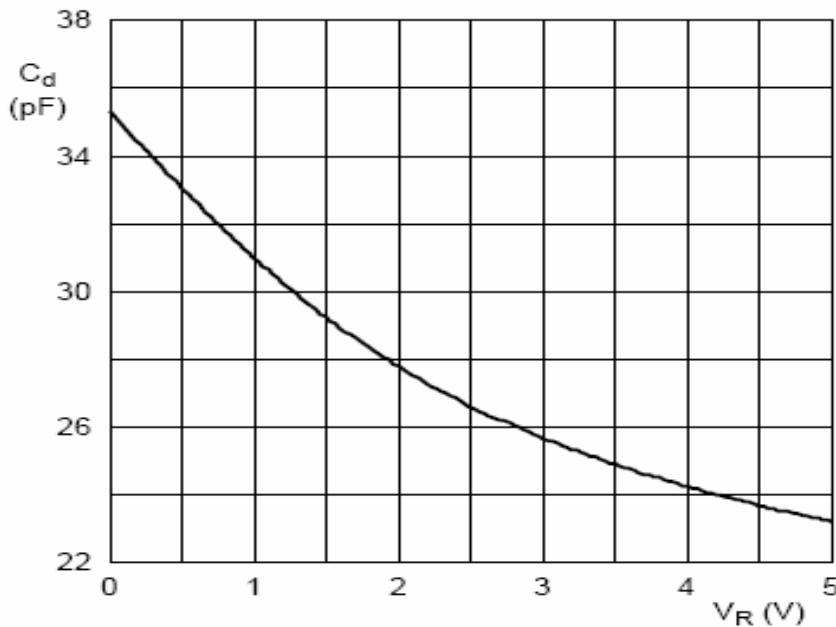
$T_{amb} = 25^\circ\text{C}$.

Relative variation of peak pulse power as a function of junction temperature; typical values.



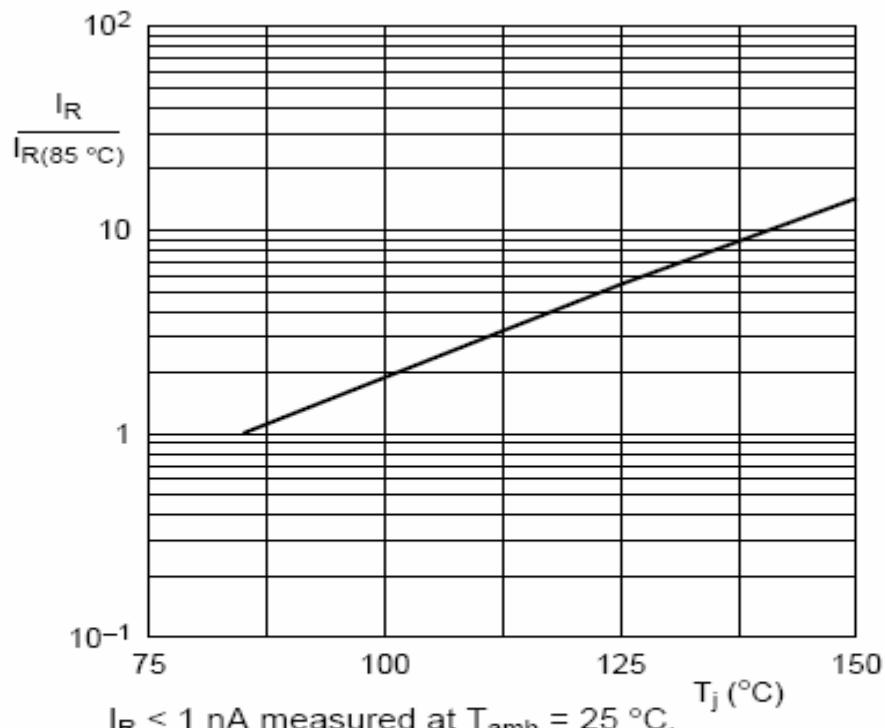
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$T_{amb} = 25 \text{ }^{\circ}\text{C}$; $f = 1 \text{ MHz}$.

Diode capacitance as a function of reverse voltage; typical values.



$I_R < 1 \text{ nA}$ measured at $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

Relative variation of reverse leakage current as a function of junction temperature; typical values.



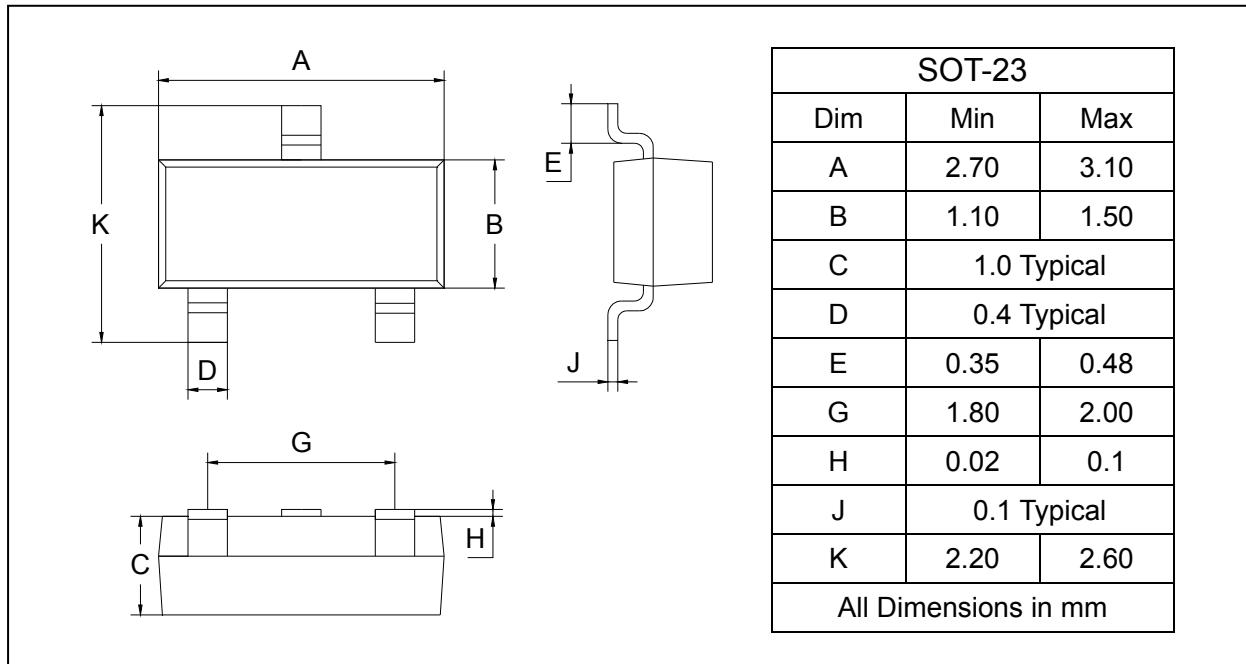
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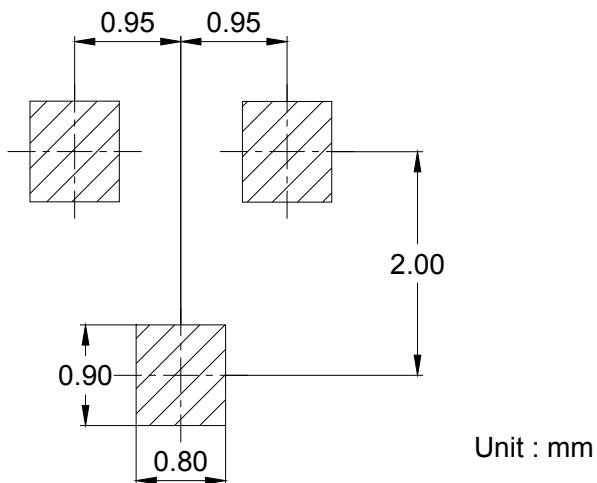
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
PESD5V0S2BT	SOT-23	3000/Tape&Reel